International Rectifier

8ETH06PbF 8ETH06FPPbF

Hyperfast Rectifier

Features

- · Hyperfast Recovery Time
- · Low Forward Voltage Drop
- · Low Leakage Current
- 175°C Operating Junction Temperature
- 2500V insulation voltage ③
- · ULE78996 approved
- Lead-Free ("PbF")

t_{rr} = 18ns typ. $I_{F(AV)}$ = 8Amp V_R = 600V

Description/Applications

State of the art Hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, Hyperfast recover time, and soft recovery.

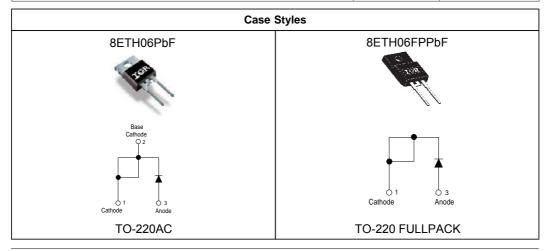
The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC Boost stage in the AC-DC section of SMPS, inverters or as freewheeling diodes.

The IR extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

Absolute Maximum Ratings

	Parameters	Max	Units
V _{RRM}	Peak Repetitive Reverse Voltage	600	V
I _{F(AV)}	Average Rectified Forward Current @ T _C = 144°C	8	A
	@T _C =108°C (FULLPACK)		
I _{FSM}	Non Repetitive Peak Surge Current @ T _J = 25°C	90	
	(FULLPACK)	100	
I _{FM}	Peak Repetitive Forward Current	16	
T _J , T _{STG}	Operating Junction and Storage Temperatures	- 65 to 175	°C



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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameters	Min	Тур	Max	Units	Test Conditions
V_{BR}, V_{r}	Breakdown Voltage, Blocking Voltage	600	-	-	V	I _R = 100μA
V _F	Forward Voltage	-	2.0	2.4	V	I _F = 8A, T _J = 25°C
		-	1.3	1.8	V	I _F = 8A, T _J = 150°C
I _R	Reverse Leakage Current	-	0.3	50	μA	V _R = V _R Rated
		-	55	500	μA	$T_J = 150$ °C, $V_R = V_R$ Rated
C _T	Junction Capacitance	-	17	-	pF	V _R = 600V
L _S	Series Inductance	-	8.0	-	nH	Measured lead to lead 5mm from package body

Dynamic Recovery Characteristics @ T_C = 25°C (unless otherwise specified)

	Parameters	Min	Тур	Max	Units	Test Conditions		
t _{rr}	Reverse Recovery Time	-	18	22	ns	$I_F = 1A$, $di_F/dt = 100A/\mu s$, $V_R = 30V$ $I_F = 8A$, $di_F/dt = 100A/\mu s$, $V_R = 30V$		
		-	20	25				
		-	25	-		T _J = 25°C		
		-	40	-		T _J = 125°C		
I _{RRM}	Peak Recovery Current	-	2.4	-	А	T _J = 25°C	I _F = 8A di _F /dt = 200A/µs	
		-	4.8	-		T _J = 125°C	V _R = 390V	
Qrr	Reverse Recovery Charge	-	25	-	nC	T _J = 25°C		
			120	-	-	T _J = 125°C		
t _{rr}	Reverse Recovery Time	-	33	-	ns		I _F = 8A	
I _{RRM}	Peak Recovery Current	-	12	-	Α	T _J = 125°C	di _F /dt = 600A/µs	
Qrr	Reverse Recovery Charge	-	220	-	nC		V _R = 390V	

Thermal - Mechanical Characteristics

	Parameters		Min	Тур	Max	Units
TJ	Max. Junction Temperature Range		-	-	175	°C
T _{Stg}	Max. Storage Temperature Range		- 65	-	175	
R _{thJC}	Thermal Resistance, Junction to Case	Per Leg	-	1.4	2	°C/W
	(Fullpa	-	3.4	4.3		
R _{thJA} ①	Thermal Resistance, Junction to Ambient	PerLeg	-	-	70	
R _{thCS} ②	Thermal Resistance, Case to Heatsink		-	0.5	-	
	Weight		-	2.0	-	g
			-	0.07	-	(oz)
	Mounting Torque		6.0	-	12	Kg-cm
			5.0	-	10	lbf.in

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Typical Socket MountMounting Surface, Flat, Smooth and Greased

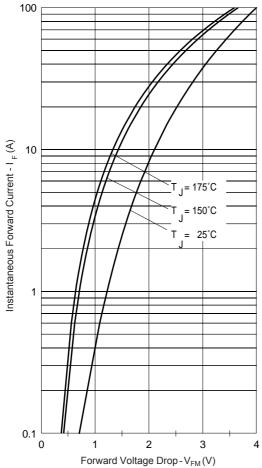


Fig. 1-Typical Forward Voltage Drop Characteristics

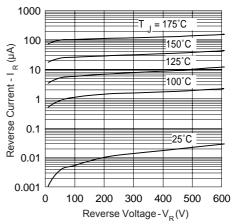


Fig. 2-Typical Values Of Reverse Current Vs. Reverse Voltage

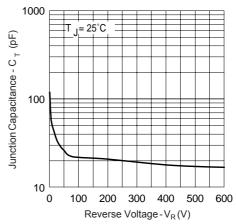


Fig.3-Typical Junction Capacitance Vs. Reverse Voltage

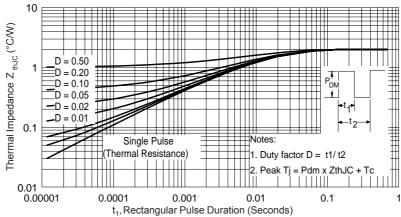


Fig. 4-Max. Thermal Impedance Z_{thJC} Characteristics

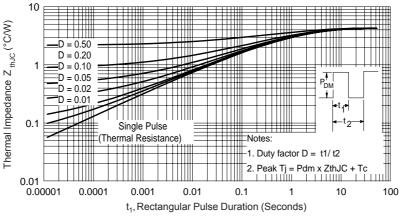


Fig. 5-Max. Thermal Impedance Z_{thJC} Characteristics (FULLPACK)

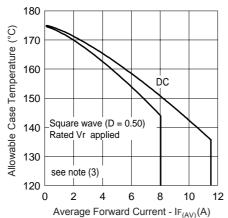


Fig. 6-Max. Allowable Case Temperature
Vs. Average Forward Current

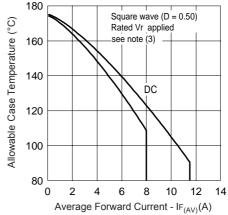


Fig. 7-Max. Allowable Case Temperature Vs. Average Forward Current (FULLPACK)

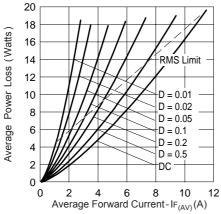


Fig. 8-Forward Power Loss Characteristics

(3) Formula used:
$$T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$$
;
 $Pd = Forward Power Loss = I_{F(AV)} \times V_{FM} @ (I_{F(AV)} / D)$
(see Fig. 8);
 $Pd_{REV} = Inverse Power Loss = V_{R1} \times I_R (1 - D)$;
 $I_R @ V_{R1} = rated V_R$

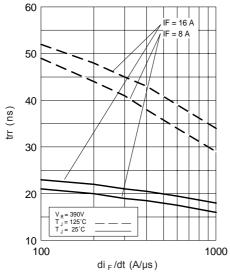


Fig. 9-Typical Reverse Recovery vs. di _F/dt

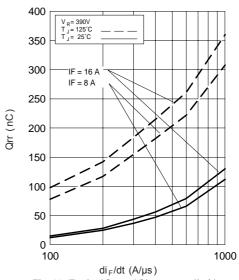


Fig. 10 - Typical Stored Charge vs. di_F/dt

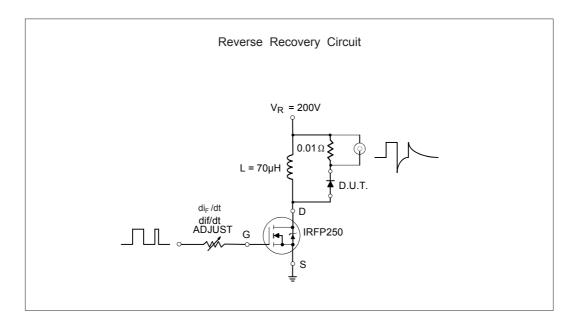


Fig. 11- Reverse Recovery Parameter Test Circuit

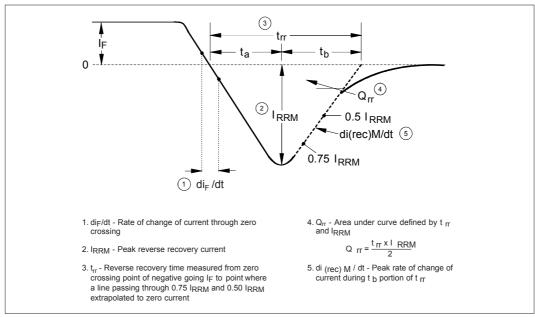
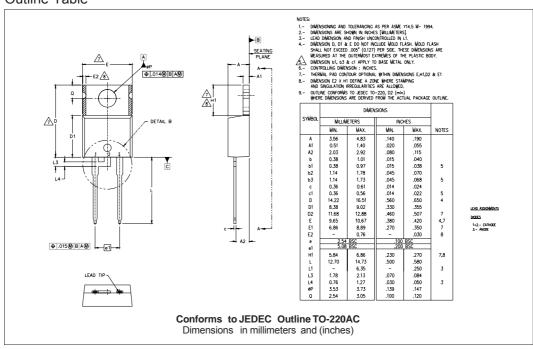
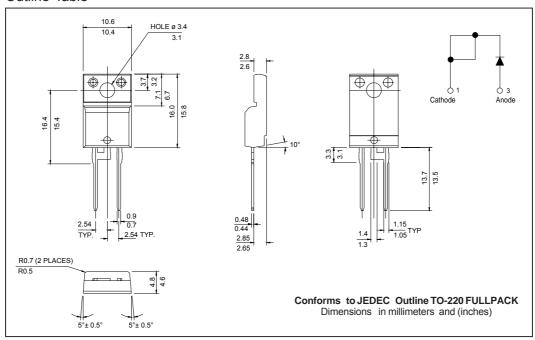


Fig. 12 - Reverse Recovery Waveform and Definitions

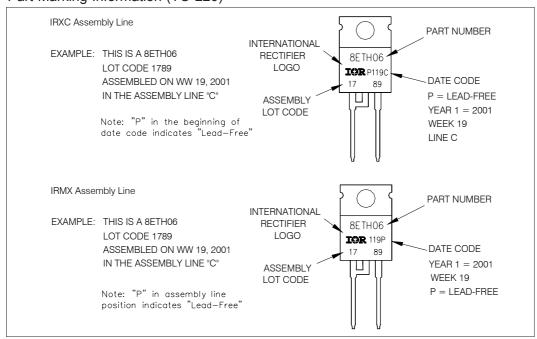
Outline Table



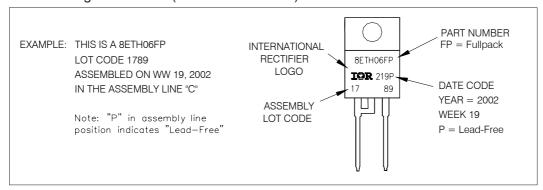
Outline Table



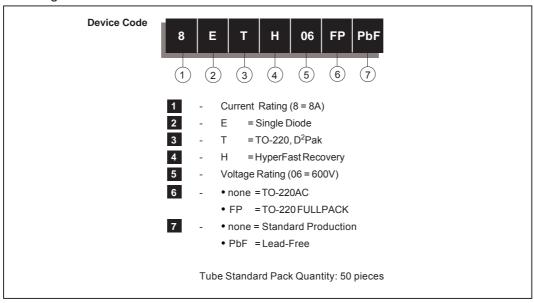
Part Marking Information (TO-220)



Part Marking Information (TO-220 FULL-PAK)



Ordering Information Table



Data and specifications subject to change without notice. This product has been designed and qualified for Industrial Level and Lead-Free. Qualification Standards can be found on IR's Web site.



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Vishay

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Document Number: 99901 www.vishay.com Revision: 12-Mar-07